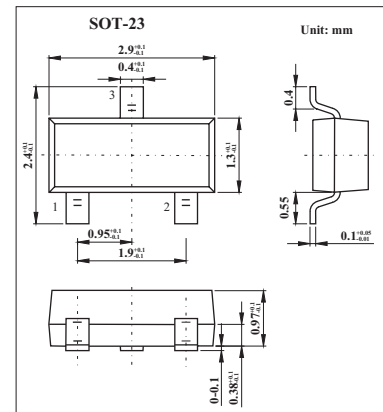


Silicon Epitaxial Schottky Barrier Diode

1SS350

■ Features

- Small interterminal capacitance ($C=0.69\text{pF typ}$).
- Low forward voltage ($V_F=0.23\text{V max}$).
- High breakdown voltage ($V_R=55\text{V}$).
- Very small-sized package permitting the 1SS350-applied sets to be made small and slim.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	5	V
Forward Current	I_F	30	mA
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F = 1\text{ mA}$			0.23	V
Forward Current	I_F	$V_F = 0.5\text{ V}$	30			mA
Reverse Current	I_R	$V_R = 0.5\text{ V}$			25	$\mu\text{ A}$
Interterminal Capacitance	C	$V_R = 0.2\text{ V}, f = 1\text{ MHz}$		0.69	0.9	pF

■ Marking

Marking	BH
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